



DH253 Hall-effect sensor is a temperature stable, stress-resistant switch. Superior high-temperature performance is made possible through a dynamic offset cancellation that utilizes chopper-stabilization. This method reduces the offset voltage normally caused by device over molding, temperature dependencies, and thermal stress.

DH 253 includes the following on a single silicon chip: voltage regulator, Hall voltage generator, small-signal amplifier, chopper stabilization, Schmitt trigger, open-drain output. Advanced CMOS wafer fabrication processing is used to take advantage of low-voltage requirements, component matching, very low input-offset errors, and small component geometries.

DH 253 is rated for operation between the ambient temperatures  $-40^{\circ}\text{C}$  and  $+85^{\circ}\text{C}$  for the E temperature range. The four package styles available provide magnetically optimized solutions for most applications. Package types SO is an SOT-23(1.1 mm nominal height), SQ is an QFN2020-3(0.55 mm nominal height), a miniature low-profile surface-mount package, while package UA is a three-lead ultra mini SIP for through-hole mounting.

The package type is in a Halogen Free version was verified by third party Lab.

## ***Features and Benefits***

- CMOS Hall IC Technology
- Solid-State Reliability much better than reed switch
- Omni polar output switches with absolute value of North or South pole from magnet
- Low power consumption(2.6mA)
- High Sensitivity for reed switch replacement
- 100% tested at  $125^{\circ}\text{C}$  for K.
- Small Size
- ESD HBM  $\pm 4\text{KV}$  Min
- COST competitive

## ***Applications***

- Solid state switch
- Lid close sensor for power supply devices
- Magnet proximity sensor for reed switch replacement in high duty cycle applications.
- Safety Key on sporting equipment
- Revolution counter
- Speed sensor
- Position Sensor
- Rotation Sensor
- Safety Key



### Absolute Maximum Ratings At ( $T_a=25^{\circ}\text{C}$ )

Characteristics	Values	Unit
Supply voltage, ( $V_{DD}$ )	7	V
Output Voltage, ( $V_{out}$ )	6	V
Reverse voltage, ( $V_{DD}$ ) ( $V_{out}$ )	-0.3	V
Magnetic flux density	Unlimited	Gauss
Output current, ( $I_{out}$ )	25	mA
Operating Temperature Range, ( $T_a$ )	"E" version	-40 to +85
	"K" version	-40 to +125
Storage temperature range, ( $T_s$ )	-55 to +150	°C
Maximum Junction Temp, ( $T_j$ )	150	°C
Thermal Resistance	( $\theta_{JA}$ ) UA / SO / SQ	206 / 543 / 543
	( $\theta_{JC}$ ) UA / SO / SQ	148 / 410 / 410
Package Power Dissipation, ( $P_D$ ) UA / SO / SQ	606 / 230 / 230	mW

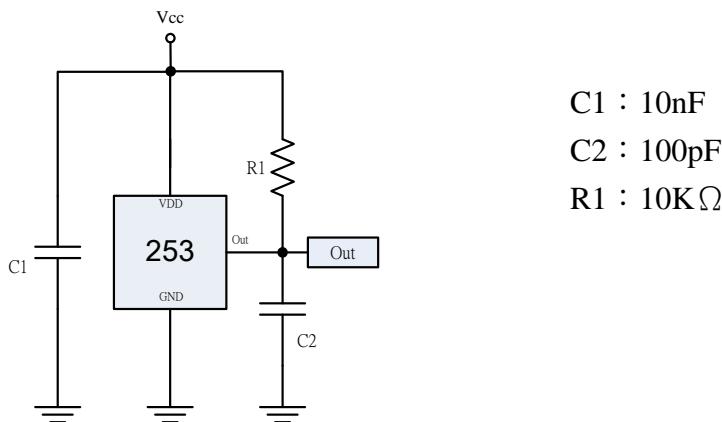
*Note:* Exceeding the absolute maximum ratings may cause permanent damage. Exposure to absolute maximum-rated conditions for extended periods may affect device reliability.

### Electrical Specifications

DC Operating Parameters  $T_a=+25^{\circ}\text{C}$ ,  $V_{DD}=5.0V$

Parameters	Test Conditions	Min	Typ	Max	Units
Supply Voltage, ( $V_{DD}$ )	Operating	2.5		6	V
Supply Current, ( $I_{DD}$ )	Average		2.6	6.0	mA
Output Low Voltage, ( $V_{DS(ON)}$ )	$I_{OUT}=10\text{mA}$			400	mV
Output Leakage Current, ( $I_{off}$ )	$I_{OFF} \quad B < B_{RP}, V_{OUT} = 5\text{V}$			10	uA
Output Rise Time, ( $T_R$ )	$R_L=10\text{k}\Omega, CL=20\text{pF}$			0.45	uS
Output Fall Time, ( $T_F$ )	$R_L=10\text{k}\Omega; CL=20\text{pF}$			0.45	uS
Electro-Static Discharge	HBM	4			KV
(B <sub>OPS</sub> ) (B <sub>OPN</sub> )	S pole to branded side, B > B <sub>OP</sub> , V <sub>out</sub> On		30	60	Gauss
	N pole to branded side, B > B <sub>OP</sub> , V <sub>out</sub> On	-60	-30		
(B <sub>RPS</sub> ) (B <sub>RPN</sub> )	S pole to branded side, B < B <sub>RP</sub> , V <sub>out</sub> Off	5	25		Gauss
	N pole to branded side, B < B <sub>RP</sub> , V <sub>out</sub> Off		-25	-5	
Hysteresis, (B <sub>HYS</sub> )	B <sub>OPx</sub> - B <sub>RPx</sub>		5		Gauss

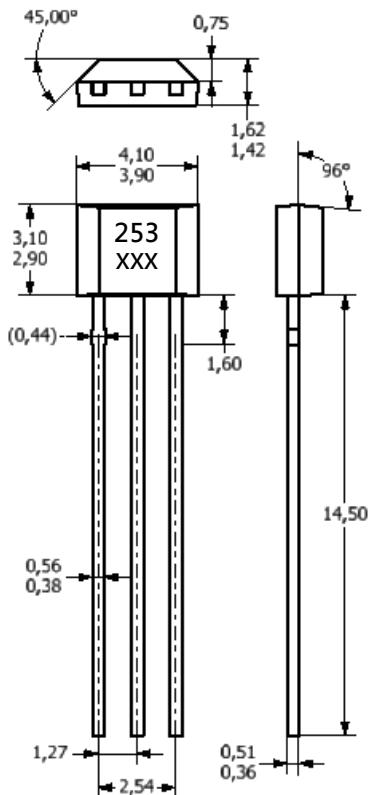
### Typical Application circuit



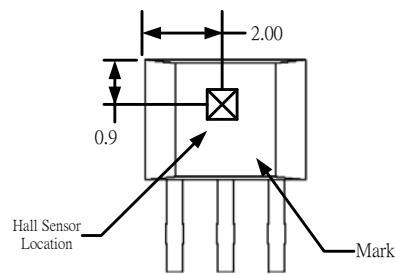


## Sensor Location, Package Dimension and Marking DH253 Package

### UA Package



### Hall Chip location

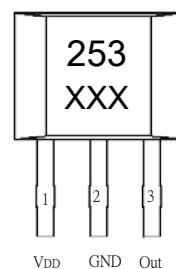


### NOTES:

- 1).Controlling dimension: mm
- 2).Leads must be free of flash and plating voids
- 3).Do not bend leads within 1 mm of lead to package interface.
- 4).PINOUT:

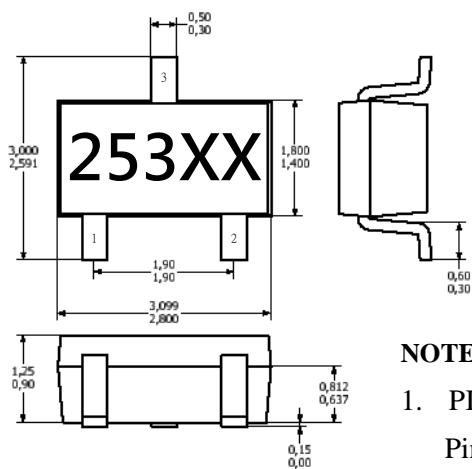
Pin 1	V <sub>DD</sub>
Pin 2	GND
Pin 3	Output

### Output Pin Assignment (Top view)

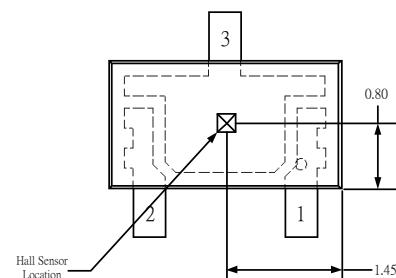


### SO Package

#### (Top View)



### Hall Plate Chip Location (Bottom view)



### NOTES:

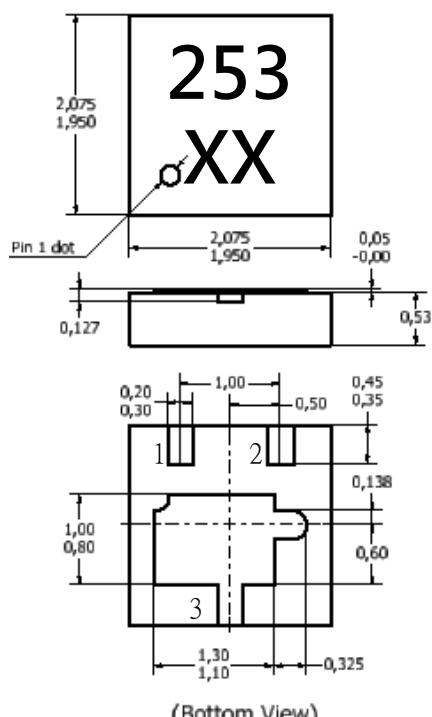
1. PINOUT (See Top View at left :)

Pin 1	V <sub>DD</sub>
Pin 2	Output
Pin 3	GND
2. Controlling dimension: mm
3. Lead thickness after solder plating will be 0.254mm maximum



### SQ Package

(Top View)



(Bottom View)

### NOTES:

1. PINOUT (See Top View at left)  
Pin 1 VDD  
Pin 2 Output  
Pin 3 GND
2. Controlling dimension:  
mm;
3. Chip rubbing will be  
10mil maximum;
4. Chip must be in PKG.  
center.

Hall Plate Chip Location

(Top view)

